

UNISONIC TECHNOLOGIES CO., LTD

2N7002W Preliminary Power MOSFET

300mA, 60V N-CHANNEL POWER MOSFET

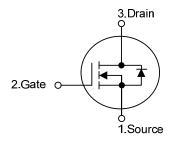
■ DESCRIPTION

The UTC **2N7002W** uses advanced technology to provide excellent $R_{\text{DS(ON)}}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

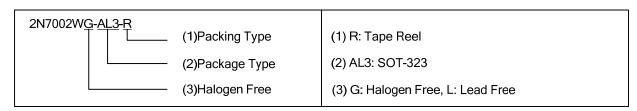
- * High Density Cell Design for Low R_{DS(ON)}.
- * Voltage Controlled Small Signal Switch
- * Rugged and Reliable
- * High Saturation Current Capability

■ SYMBOL

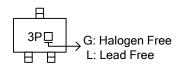


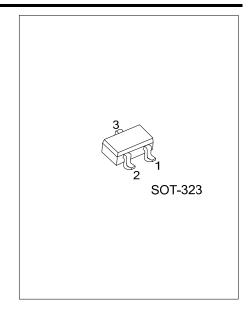
ORDERING INFORMATION

| Ordering Number | | Dookogo | Pin Assignment | | | Dooking |
|-----------------|----------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing |
| 2N7002WL-AL3-R | 2N7002WG-AL3-R | SOT-323 | S | G | D | Tape Reel |



MARKING





■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified.)

| PARAMETER | | SYMBOL | RATINGS | UNIT | |
|---|--------------------------------------|----------------|------------|-------|--|
| Drain-Source Voltage | | V_{DSS} | 60 | V | |
| Drain-Gate Voltage (R _{GS} ≤1MΩ) | | V_{DGR} | 60 | V | |
| Gate Source Voltage | Continuous | \/ | ±20 | V | |
| | Non Repetitive(t _P <50µs) | V_{GSS} | ±40 | | |
| Drain Current | Continuous | _ | 300 | mA | |
| Diaili Cultent | Pulsed | I _D | 800 | | |
| Power Dissipation | | D | 200 | mW | |
| Derated Above 25°C | | P_D | 1.6 | mW/°C | |
| Junction Temperature | | T_J | + 150 | °C | |
| Storage Temperature | | T_{STG} | -55 ~ +150 | °C | |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|---------------|-------------|------|
| Junction to Ambient | θ_{JA} | 625 (Note1) | °C/W |

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | | |
|---|----------------------|--|--------|------|------|------|--|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V_{GS} =0V, I_D =10 μ A | 60 | | | V | | |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | | | 1 | μΑ | | |
| Gate-Source Leakage Current | I_{GSSF} | V _{GS} =20V, V _{DS} =0V | | | 100 | nA | | |
| Gate-Source Leakage Current | I_{GSSR} | V_{GS} =-20V, V_{DS} =0V | | | -100 | nA | | |
| ON CHARACTERISTICS (Note2) | | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}$, $I_D = 250 \mu A$ | 1 | 2.1 | 2.5 | V | | |
| Drain-Source On-Voltage | V _{DS (ON)} | $V_{GS} = 10V, I_D = 300mA$ | 0.6 3. | | 3.75 | V | | |
| Dialii-Source Oil-Voltage | | $V_{GS} = 5.0V, I_{D} = 50mA$ | | 0.09 | 1.5 | V | | |
| Static Drain-Source On-Resistance | D | V _{GS} =10V, I _D =300mA ,T _J =125°C | | | 13.5 | Ω | | |
| Static Drain-Source On-Resistance | R _{DS (ON)} | V_{GS} =5.0V, I_D =50mA | | | 7.5 | Ω | | |
| DYNAMIC CHARACTERISTICS | | | | | | | | |
| Input Capacitance | C _{ISS} | V_{DS} =25V, V_{GS} =0V,f=1.0MHz | | 20 | 50 | pF | | |
| Output Capacitance | Coss | | | 11 | 25 | pF | | |
| Reverse Transfer Capacitance | C _{RSS} | | | 4 | 5 | pF | | |
| Turn-On Time | 4 | V_{DD} =30V, R_L =150 Ω , I_D =200mA, | | 20 | | nS | | |
| Turn-On Time | t _{ON} | V_{GS} =10V, R_{GEN} =25 Ω | | | 20 | 113 | | |
| Turn-Off Time | toff | V_{DD} =30V, R_L =25 Ω , I_D =200mA, | | | 20 | nS | | |
| Turn-On Time | UOFF | V_{GS} =10V, R_{GEN} =25 Ω | | | 20 | | | |
| DRAIN-SOURCE DIODE CHARACTE | RISTICS AN | ID MAXIMUM RATINGS | | | | | | |
| Drain-Source Diode Forward Voltage | V_{SD} | V _{GS} =0V, Is=300mA (Note) | | 0.88 | 1.5 | V | | |
| Maximum Pulsed Drain-Source Diode | | | | | 0.8 | Α | | |
| Forward Current | I _{SM} | | | | 0.0 | | | |
| Maximum Continuous Drain-Source Diode Forward Current | ls | | | | 300 | mA | | |

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

2. Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%

TEST CIRCUIT AND WAVEFORM

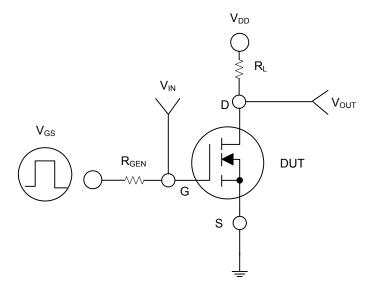


Fig. 1

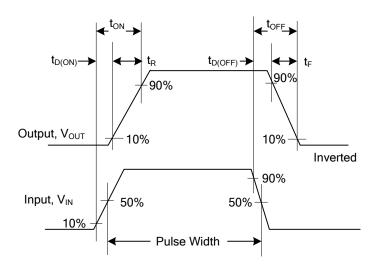


Fig. 2 Switching Waveforms

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